In accordance with the guidelines and waived provisions of 37 C.F.R. 1.121 promulgated in the USPTO announcement of January 31, 2003, please make the following amendments.

IN THE CLAIMS:

Please amend the claims as follows.

1.-24. (Withdrawn)

25. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming an interlayer insulating film on a thin film transistor formed on an insulator;

forming a first insulating film on the interlayer insulating film;

forming a wiring line on the first insulating film;

forming an anode electrically connected to the thin film transistor through the wiring line, on the first insulating film;

forming a resin insulating film that covers the anode and the wiring line;

etching the resin insulating film to form a bank;

conducting heat treatment to the ~~resin insulating film~~ bank;

wiping the anode;

forming a second insulating film to cover the anode and the bank;

forming an organic compound layer on the second insulating film; and

forming a cathode on the organic compound layer.

26. (Original) A method of manufacturing a light emitting device according to claim 25, wherein plasma treatment is performed on the bank.

27. (Currently Amended) A method of manufacturing a light emitting device according to claim 25, wherein plasma treatment is carried out in at least one ~~or more~~ kinds of gas selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and ~~rare~~ noble gas.

28. (Original) A method of manufacturing a light emitting device according to claim 25, wherein the step of wiping the anode uses a PVA-based porous material.

29. (Original) A method of manufacturing a light emitting device according to claim 25, wherein the step of wiping the anode is a step for leveling the surface of the anode.

30. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming an interlayer insulating film on a thin film transistor formed on an insulator;

forming a first insulating film on the interlayer insulating film;

forming a wiring line on the first insulating film;

forming an anode electrically connected to the thin film transistor through the wiring line, on the first insulating film;

conducting first heat treatment to the anode;

forming a resin insulating film that covers the anode and the wiring line, and etching the resin insulating film to form a bank;

conducting second heat treatment to the [resin insulating film] bank;

wiping the anode;

forming a second insulating film to cover the anode and the bank;

forming an organic compound layer on the second insulating film; and

forming a cathode on the organic compound layer.

31. (Original) A method of manufacturing a light emitting device according to claim 30, wherein plasma treatment is performed on the bank.

32. (Currently Amended) A method of manufacturing a light emitting device according to claim 30, wherein plasma treatment is carried out in at least one ~~or more~~ kinds of gas selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and ~~rare~~ noble gas.

33. A method of manufacturing a light emitting device according to claim 30, wherein the step of wiping the anode uses a PVA-based porous material.

34. (Original) A method of manufacturing a light emitting device according to claim 30, wherein the step of wiping the anode is a step for leveling the surface of the anode.

35. (Original) A method of manufacturing a light emitting device comprising the steps of:

forming an interlayer insulating film on a thin film transistor formed on an insulator;

forming a first insulating film on the interlayer insulating film;

forming a wiring line;

forming an anode electrically connected to the thin film transistor through the wiring line;

conducting first heat treatment to the anode;

forming a resin insulating film that covers the anode and the wiring line, which serves a bank;

conducting second heat treatment to the resin insulating film;

etching the resin insulating film to form a bank;

wiping the anode;

forming an insulating film to cover the anode and the bank;

forming an organic compound layer on the insulating film, and forming a cathode on the organic compound layer.

36. (Original) A method of manufacturing a light emitting device according to claim 35, wherein plasma treatment is performed on the bank.

37. (Currently Amended) A method of manufacturing a light emitting device according to claim 35, wherein plasma treatment is carried out in at least one ~~or more~~ kinds of gas selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and ~~rare~~ noble gas.

38. (Original) A method of manufacturing a light emitting device according to claim 35, wherein the step of wiping the anode uses a PVA-based porous material.

39. (Original) A method of manufacturing a light emitting device according to claim 35, wherein the step of wiping the anode is a step for leveling the surface of the anode.

40. (Currently Amended) A method of manufacturing a light emitting device comprising the steps of:

forming an interlayer insulating film on a thin film transistor formed on an insulator;

performing plasma treatment on a surface of the interlayer insulating film;

forming a wiring line;

forming an anode electrically connected to the thin film transistor through the wiring line;

forming a resin insulating film that covers the anode and the wiring line;

etching the resin insulating film to form a bank;

conducting heat treatment to the [resin insulating film] bank;

wiping the anode;

forming an insulating film to cover the anode and the bank;

forming an organic compound layer on the insulating film; and

forming a cathode on the organic compound layer.

41. (Currently Amended) A method of manufacturing a light emitting device according to claim 40, wherein the plasma treatment is performed on the bank.

42. (Currently Amended) A method of manufacturing a light emitting device according to claim 40, wherein the plasma treatment is carried out in one or more kinds of gas selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and ~~rare~~ noble gas.

43. (Original) A method of manufacturing a light emitting device according to claim 40, wherein the step of wiping the anode uses a PVA-based porous material.

44. (Original) A method of manufacturing a light emitting device according to claim 40, wherein the step of wiping the anode is a step for leveling the surface of the anode.

45. (Original) A method of manufacturing a light emitting device comprising the steps of:

forming an interlayer insulating film on a thin film transistor, the thin film transistor being formed on a substrate having an insulating surface;

performing plasma treatment on a surface of the interlayer insulating film;

forming an anode over the interlayer insulating film,

forming a wiring line over the interlayer insulating film;

forming a resin insulating film that covers the anode, the wiring line and the interlayer insulating film;

moving the substrate on which the thin film transistor is formed from a first 15 processing room to a second processing room;

etching the resin insulating film to form a bank;

conducting heat treatment;

performing plasma treatment on a surface of the bank;

wiping the anode;

forming an insulating film to cover the anode and the bank;

forming an organic compound layer on the insulating film; and

forming a cathode on the organic compound layer.

46. (Original) A method of manufacturing a light emitting device according to claim 45, wherein the anode partially overlaps the wiring line so that the anode is electrically connected to the thin film transistor.

47. (Currently Amended) A method of manufacturing a light emitting device according to claim 45, wherein plasma treatment is carried out in one or more kinds of gas selected from the group consisting of hydrogen, nitrogen, halogenated carbon, hydrogen fluoride, and ~~rare~~ noble gas.

48. (Original) A method of manufacturing a light emitting device according to claim 45, wherein the step of wiping the anode uses a PVA-based porous material.

49. (Original) A method of manufacturing a light emitting device according to claim 45, wherein the step of wiping the anode is a step for leveling the surface of the anode.

50. (Previously Amended) A method of manufacturing a device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting the electrode with the thin film transistor, over the interlayer insulating film;

forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

51. (Currently Amended) A method of manufacturing a ~~light emitting~~ device according to claim 50, wherein the electrode is an anode or a cathode.

52. (Previously Amended) A method of manufacturing a device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting the electrode with the thin film transistor, over the interlayer insulating film;

forming a resin insulating film over the anode, the wiring line and the interlayer insulating film;

forming a film for preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage.

53. (Currently Amended) A method of manufacturing a ~~light emitting~~ device according to claim 52, wherein the electrode is an anode or a cathode.

54. (Previously Amended) A method of manufacturing a device according to claim 52, wherein the film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester,

polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine, N,N-Bis(2-hydroxyethyl)alkylamine, alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether.

55. (Currently Amended) A method of manufacturing a ~~light emitting~~ device according to claim 54, wherein the film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material formed by spin coating or evaporation.

56. (Currently Amended) A method of manufacturing a ~~light emitting~~ device according to claim 52, wherein the film for preventing the substrate from contamination and electrostatic discharge damage comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

57. (Currently Amended) A method of manufacturing a ~~light emitting~~ device according to claim 53, wherein the method further comprises the steps of removing the film, etching the resin insulating film to form a bank, wiping the anode, forming an organic compound layer over the bank and the anode.

58. (Original) A method of manufacturing a device comprising the steps of:

removing an anti-electrostatic film formed on a resin insulating film, the resin insulating film formed over a thin film transistor and anode;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the anode;

forming a cathode on the organic compound layer.

59. (Previously Amended) A method of manufacturing a device according to claim 58, wherein the film for preventing the substrate from contamination and electrostatic discharge damage is an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine, N,N-Bis(2-hydroxyethyl)alkylamine, alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl ether.

60. (Currently Amended) A method of manufacturing a ~~light emitting~~ device according to claim 59, wherein the organic conductive material is formed by spin coating or evaporation.

61. (Currently Amended) A method of manufacturing a ~~light emitting~~ device according to claim 58, wherein the anti-electrostatic film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

62. (Previously Added) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting to the electrode over the interlayer insulating film;

forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film; and

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

63. (Previously Added) A method of manufacturing a light emitting device according to claim 62, wherein the film formed over the resin insulating film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine, N, N-Bis (2-hydroxyethyl)alkylamine, alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkylsulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

64. (Previously Added) A method of manufacturing a light emitting device according to claim 62, wherein the film formed over the resin insulating film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

65. (Previously Added) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a first electrode over the interlayer insulating film;

forming a wiring line connecting to the first electrode over the interlayer insulating film;

forming a resin insulating film over the first electrode, the wiring line and the interlayer insulating film;

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

66. (Previously Amended) A method of manufacturing a light emitting device according to claim 65, wherein the film formed over the resin insulating film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine, N, N-Bis(2-hydroxyethyl)alkylamine, alkyl-diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

67. (Previously Added) A method of manufacturing a light emitting device according to claim 65, wherein the film formed over the resin insulating film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

68. (Previously Added) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting the electrode over the interlayer insulating film;

forming a resin insulating film over the anode, the wiring line and the interlayer insulating film;

forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage.

69. (Previously Added) A method of manufacturing a light emitting device according to claim 68, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine, N,N-Bis(2-hydroxyethyl) alkylamine, alkyldiethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkyl benzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

70. (Previously Added) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting to the electrode over the interlayer insulating film;

forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film; and

forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

71. (Currently Amended) A method of manufacturing a light emitting device according to claim 70, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine, N,N-Bis(2-hydroxyethyl)alkylamine, alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate , alkyl phosphate, tetraalkylammonium salt, trialky lbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

72. (Previously Added) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a first electrode over the interlayer insulating film;

forming a wiring line connecting to the first electrode over the interlayer insulating film;

forming a resin insulating film over the first electrode, the wiring line and the interlayer insulating film;

forming a film comprising an organic conductive material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

73. (Previously Added) A method of manufacturing a light emitting device according to claim 72, wherein the organic conductive material is selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine, N,N-Bis(2-hydroxyethyl)alkylamine, alkyl diethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate,alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkyl benzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

74. (Previously Added) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting the electrode over the interlayer insulating film;

forming a resin insulating film over the anode, the wiring line and the interlayer insulating film;

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage.

75. (Previously Added) A method of manufacturing a light emitting device according to claim 74, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

76. (Previously Added) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting to the electrode over the interlayer insulating film;

forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film; and

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

77. (Previously Added) A method of manufacturing a light emitting device according to claim 76, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or

benzocyclobutene.

78. (Previously Added) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

forming a first electrode over the interlayer insulating film;

forming a wiring line connecting to the first electrode over the interlayer insulating film;

forming a resin insulating film over the first electrode, the wiring line and the interlayer insulating film;

forming a film comprising an organic insulating material over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room;

removing the film;

etching the resin insulating film to form a bank;

baking the bank in a vacuum;

forming an organic compound layer over the bank and the first electrode;

forming a second electrode on the organic compound layer.

79. (Previously Added) A method of manufacturing a light emitting device according to claim 78, wherein the organic insulating material is selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.

80. (Previously Added) A method of manufacturing a light emitting device comprising the steps of:

forming a thin film transistor formed over a substrate having an insulating surface;

forming an interlayer insulating film over the thin film transistor;

performing plasma treatment on a surface of the interlayer insulating film;

forming an electrode over the interlayer insulating film;

forming a wiring line connecting to the electrode over the interlayer insulating film;

forming a resin insulating film over the electrode, the wiring line and the interlayer insulating film; and

forming a film over the resin insulating film, the film preventing the substrate over which the thin film transistor is formed from a contamination and an electrostatic discharge damage;

moving the substrate over which the thin film transistor is formed from a first processing room to a second processing room.

81. (Previously Added) A method of manufacturing a light emitting device according to claim 80, wherein the film formed over the resin insulating film comprises an organic conductive material selected from the group consisting of polyethylene dioxythiophene, polyaniline, glycerin fatty acid ester, polyoxyethylene alkyl ether, N-2-Hydroxyethyl-N-2-hydroxyalkylamine, N,N-Bis(2-hydroxyethyl) alkylamine [alkyl diethanolamine], alkyldiethanolamide, polyoxyethylene alkylamine, polyoxyethylene alkylamine fatty acid ester, alkyl sulfonate, alkylbenzenesulfonate, alkyl phosphate, tetraalkylammonium salt, trialkylbenzylammonium salt, alkyl betaine, alkyl imidazolium betaine, and polyoxyethylene alkylphenyl.

82. (Previously Added) A method of manufacturing a light emitting device according to claim 80, wherein the film comprises an organic insulating material selected from the group consisting of polyimide, acrylic, polyamide, polyimideamide, or benzocyclobutene.